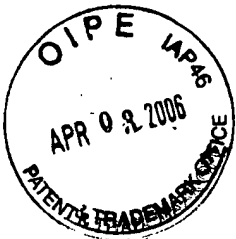


IFW



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yang, et al. Docket No.: TSM03-0929  
Serial No.: 10/823,158 Art Unit: 2814  
Filed: April 13, 2004 Examiner: Theresa T. Doan  
For: Methods and Structures for Planar and Multiple-Gate Transistors Formed on SOI

**Certificate of Mailing via First Class Mail (37 C.F.R. § 1.8(a))**

Date of Deposit: March 29, 2006

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Respectfully submitted,

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